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International Standard IEC 60747-4 has been prepared by subcommittee 47E: Discrete semiconductor devices, of IEC technical committee 47: Semiconductor devices. This second edition cancels and replaces the first edition, published in 1991, its amendments

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Edition: 3.1 Published: 09/23/2019 Number of Pages: 418 File Size: 1 file , 5.1 MB Document History. IEC 60747-7 Ed. 3.1 b:2019 currently viewing. September 2019 Semiconductor devices - Discrete devices - Part 7: Bipolar transistors

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b) "Clause 4 Terminology and letter symbols" was divided into "Clause 3 Terms and definitions" and "Clause 4 Letter symbols" was amended with additions and deletions. c) Clause 5, 6 and 7 were amended with necessary additions and deletions. This publication is to be read in conjunction with IEC 60747-1:2006.

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